



**/ Absolute Maximum Ratings(T<sub>a</sub>=25 )**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Drain Current - Continuous	I <sub>D</sub>	32	A
Drain Current – Pulsed	I <sub>DM</sub>	128	A
Gate-Source Voltage	V <sub>GS</sub>	± 20	V
Power Dissipation	P <sub>D</sub> (T <sub>c</sub> =25 )	26	W
Single Pulse Avalanche Energy(L=0.5mH)	E <sub>AS</sub>	274	mJ
Avalanche Current(L=0.5mH)	I <sub>AS</sub>	28	A
Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	
Thermal resistance, junction - ambient	t 10s	R <sub>JA</sub>	/ W
	Steady-State		
Thermal resistance, junction - case	Steady-State	R <sub>JC</sub>	55
			4.8

**/ Electrical Characteristics(T<sub>a</sub>=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	30	33		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1.0	uA
Gate-Body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.5	3	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		3.7	4.5	m
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A		5.1	6	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1.2	V
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V V <sub>GS</sub> =0V f=1.0MHz		2500		pF
Output Capacitance	C <sub>oss</sub>			280		
Reverse Transfer Capacitance	C <sub>rss</sub>			210		
Gate resistance	R <sub>g</sub>	V <sub>GS</sub> =0V V <sub>DS</sub> =0V f=1MHz		3.3		Ω
Total Gate Charge	Q <sub>g(10V)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		30		nC
Total Gate Charge	Q <sub>g(4.5V)</sub>			13.5		
Gate Source Charge	Q <sub>gs</sub>			5.5		
Gate Drain Charge	Q <sub>gd</sub>			3.5		

**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75$ $R_{GEN}=3$		8		ns
Turn-On Rise Time	$t_r$			3		
Turn-Off Delay Time	$t_{d(off)}$			34		
Turn-Off Fall Time	$t_f$			5.5		

/ Electrical Characteristic Curve

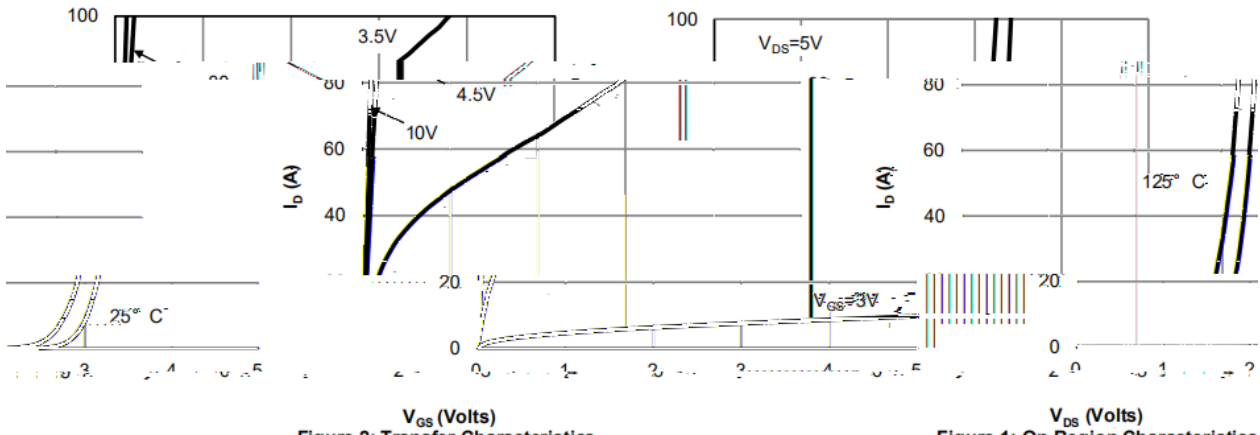


Figure 2: Transfer Characteristics

Figure 1: On-Region Characteristics

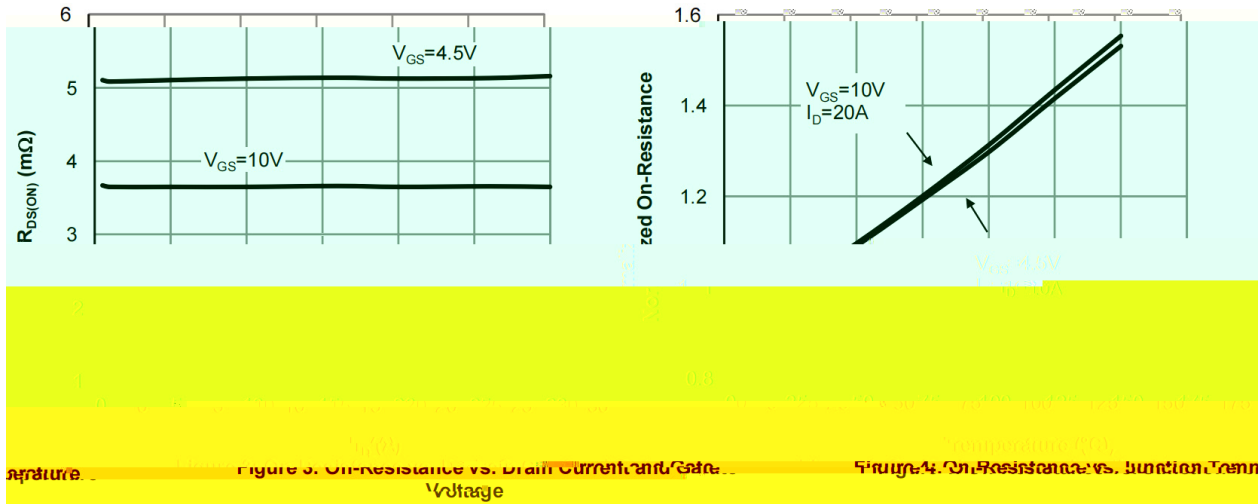


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Drain Current

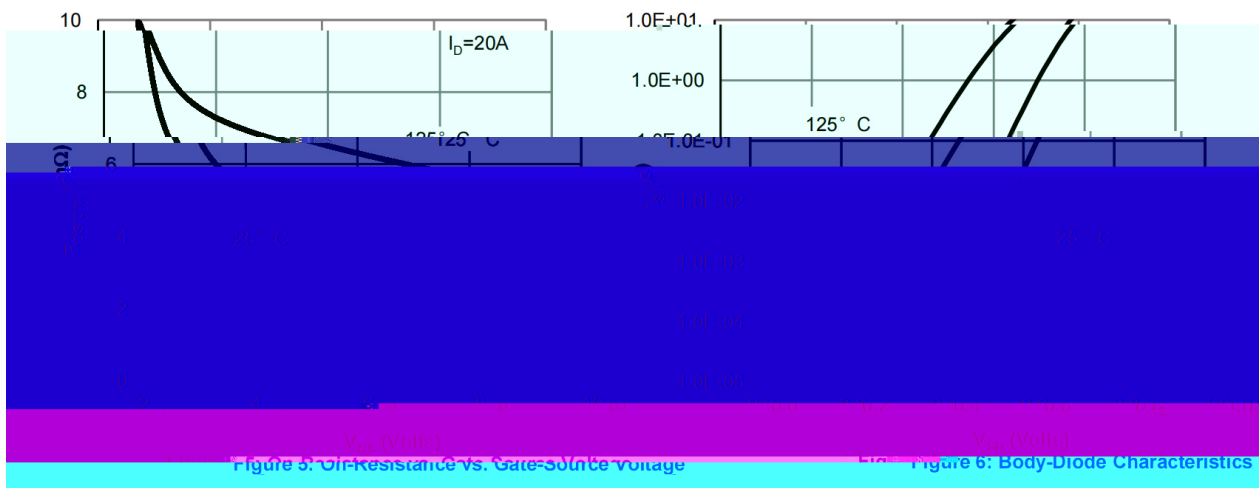


Figure 5: On-Resistance vs. Gate-Source Voltage

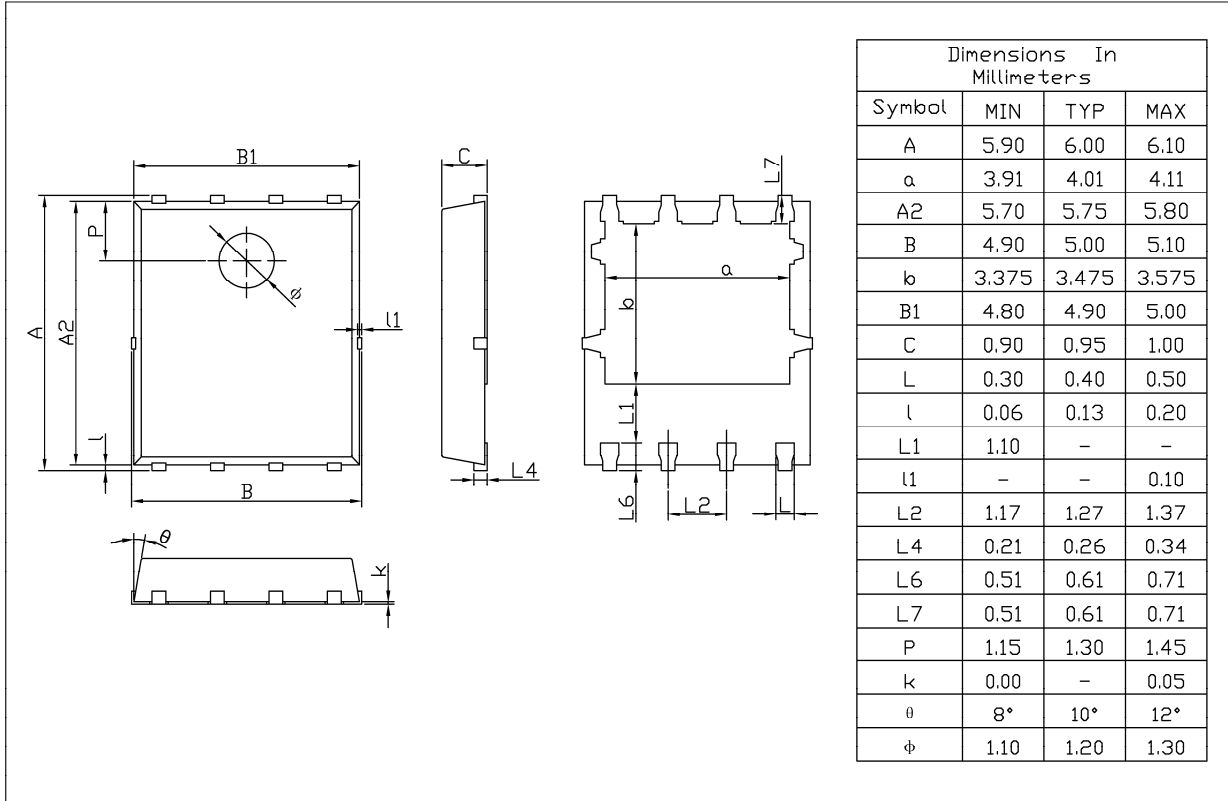
Figure 6: Body-Diode Characteristics

**BRCS050N03ZC**  
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**/ Package Dimensions**

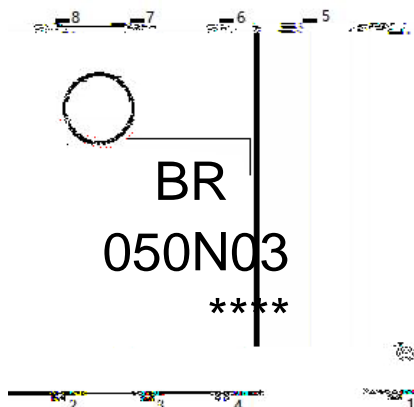
PDFN5 X6

Unit:mm



Rev.02 202510

**/ Marking Instructions**



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Note

BR

Company Code

050N03

Product Type Code

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Lot No. Code, code change with Lot No.

